

APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention	METHOD FOR FABRICATING A SEMICONDUCTOR TRANSISTOR DEVICE HAVING ULTRA-SHALLOW SOURCE/DRAIN EXTENSIONS
Application Type : regular, utility Attorney Docket Number : NAUP0591USA	
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as our attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.